

# Dimitris E Ioannou

## List of Publications by Year in descending order

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21  
papers

384  
citations

933264

10  
h-index

1199470

12  
g-index

21  
all docs

21  
docs citations

21  
times ranked

493  
citing authors

#	ARTICLE	IF	CITATIONS
1	Topological Insulator Bi <sub>2</sub> Se <sub>3</sub> Nanowire High Performance Field-Effect Transistors. Scientific Reports, 2013, 3, .	1.6	73
2	Field Effect Diode (FED): A novel device for ESD protection in deep sub-micron SOI technologies. , 2006, , .		57
3	SOI Field-Effect Diode DRAM Cell: Design and Operation. IEEE Electron Device Letters, 2013, 34, 1002-1004.	2.2	49
4	Design and optimization of the SOI field effect diode (FED) for ESD protection. Solid-State Electronics, 2008, 52, 1482-1485.	0.8	30
5	Scaling of the SOI field effect diode (FED) for memory application. , 2009, , .		27
6	Effect of Floating-Body and Stress Bias on NBTI and HCI on 65-nm SOI pMOSFETs. IEEE Electron Device Letters, 2008, 29, 262-264.	2.2	22
7	High-performance room-temperature TiO <sub>2</sub> -functionalized GaN nanowire gas sensors. Applied Physics Letters, 2019, 115, .	1.5	22
8	SOI FED-SRAM Cell: Structure and Operation. IEEE Transactions on Electron Devices, 2015, 62, 2865-2870.	1.6	21
9	Non-volatile memory with self-assembled ferrocene charge trapping layer. Applied Physics Letters, 2013, 103, .	1.5	19
10	Precise gas discrimination with cross-reactive graphene and metal oxide sensor arrays. Applied Physics Letters, 2018, 113, .	1.5	16
11	On the Nature of the Memory Mechanism of Gated-Thyristor Dynamic-RAM Cells. IEEE Journal of the Electron Devices Society, 2015, 3, 468-471.	1.2	15
12	Ferroelectricity in Polar Polymer-Based FETs: A Hysteresis Analysis. Advanced Functional Materials, 2018, 28, 1705250.	7.8	14
13	Degradation of High- $k$ /Metal Gate nMOSFETs Under ESD-Like Stress in a 32-nm Technology. IEEE Transactions on Device and Materials Reliability, 2011, 11, 118-125.	1.5	8
14	Design and analysis of multi-gate field-effect-diodes for embedded memory. , 2011, , .		3
15	Steep subthreshold slope nanowire FETs with gate-induced Schottky-barrier tunneling. , 2009, , .		2
16	High performance topological insulator nanowire field-effect transistors. , 2013, , .		2
17	On the T-RAM and FED-RAM memory mechanism. , 2015, , .		2
18	Highly Efficient Rapid Annealing of Thin Polar Polymer Film Ferroelectric Devices at Sub-Glass Transition Temperature. Advanced Functional Materials, 2018, 28, 1704165.	7.8	2

#	ARTICLE	IF	CITATIONS
19	Methods to Characterize the Electrical and Mechanical Properties of Si Nanowires. AIP Conference Proceedings, 2007, , .	0.3	0
20	Self-aligned multi-channel silicon nanowire field-effect transistors. , 2011, , .		0
21	Glassy-electret random access memory - A naturally nanoscale memory concept. , 2018, , .		0